

CLAIMS

1. A semiconductor polishing composition comprising:
fumed silica, the semiconductor polishing composition
being an aqueous dispersion solution of fumed silica,
wherein a content of the fumed silica having a particle
diameter of 100 nm or less is 15% by volume or more based on
a total amount of the fumed silica.
2. The semiconductor polishing composition of claim 1,
wherein a content of fumed silica having a particle diameter
of 100 nm or less is in a range of 15 to 90% by volume based
on a total amount of the fumed silica.
3. The semiconductor polishing composition of claim 1 or
2, wherein, in a particle size distribution by volume of the
fumed silica, the semiconductor polishing composition has a
particle size of the maximum frequency in a range of 115 nm
or less.
4. The semiconductor polishing composition of any one of
claims 1 to 3, wherein, in a particle size distribution by volume
of the fumed silica, the semiconductor polishing composition
has a particle size of the maximum frequency in a range of 80
to 115 nm.

5. The semiconductor polishing composition of any one of claims 1 to 4, wherein a content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the composition.

6. The semiconductor polishing composition of any one of claims 1 to 5, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

7. The semiconductor polishing composition of claim 6, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.